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## INFORMATION DISCLOSURE STATEMENT

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APPLICANT(S)

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FILING DATE

February 13, 2002

GROUP ART UNIT  
2818

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
DV	AA	4,686,758	08/18/87	Liu et al.	437	34	
	AB	4,952,526	08/28/90	Pribat et al.	437	89	
	AC	5,038,183	08/06/91	Kishi et al.	357	13	
	AD	5,276,343	01/04/94	Kumagai et al.	257	306	
	AE	5,422,299	06/06/95	Neudeck et al.	437	63	
DV	AF	5,425,808	06/20/95	Tokunaga et al.	117	95	
	AG						
	AH						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AI							
	AJ							

## OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

DV	AK	Philips Research Laboratories, N.V. Philips Gloeilampenfabrieken, Eindhoven, "Selective Epitaxial Deposition of Silicon", Nature No. 4840, August 4, 1962, pp. 485-486.
	AL	Rai-Choudhury P. et al., "Selective Growth of Epitaxial Silicon and Gallium Arsenide", Westinghouse Research Laboratories, Pittsburgh, Pennsylvania, January 1971, pp. 107-110.
	AM	Siekkinen J. W. et al., "SEG/ELO Material Characterization Using Silicon Bipolar Transistors", IEEE Bipolar Circuits & Technology Meeting, September 12-13, 1988, pp. 237-240.
DV	AN	Siekkinen J.W. et al., "Selective Epitaxial Growth Silicon Bipolar Transistors for Material Characterization", IEEE Transactions on Electron Devices, Vol. 35, No. 10, October 1988, pp. 1640-1644.

EXAMINER

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\* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).